



EN: This Datasheet/Document is presented by the manufacturer.

Please visit our website for pricing and availability at www.hestore.hu.

2SD2396

Transistor, NPN

Features

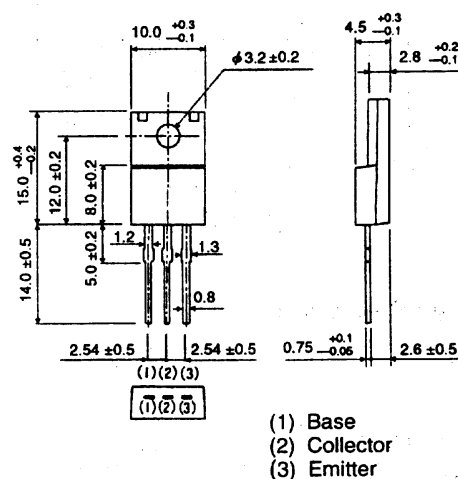
- available in TO-220FN package
- high dc current gain (h_{FE}), typically $h_{FE} = 1000$
- low collector saturation voltage, typically $V_{CE(sat)} = 0.3$ V at $I_C/I_B = 2$ A/ 0.05 A
- large collector power dissipation: $P_C = 30$ W at $T_C = 25^\circ\text{C}$
- easily insulated from the heat sink as the fin is molded
- 2 mm lower than ROHM'S TO-220FP package which allows higher density mounting
- wide safe operating area (SOA)

Applications

- low frequency power amplifier

Dimensions (Units : mm)

2SD2396 (TO-220FN)



Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit	Conditions
Collector-to-base voltage	V_{CBO}	80	V	
Collector-to-emitter voltage	V_{CEO}	60	V	
Emitter-to-base voltage	V_{EBO}	6	V	
Collector current	I_C	3	A	Continuous (dc)
	I_{CP}	6	A	Single pulse, $P_W = 100$ ms
Collector dissipation	P_C	2	W	
		30	W	$T_C = 25^\circ\text{C}$
Junction temperature	T_J	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$	

ROHM

2SD2396 Transistor, NPN, 2SD series

Electrical characteristics (unless otherwise noted, $T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min	Typical	Max	Unit	Conditions
Collector-to-base breakdown voltage	BV_{CBO}	80			V	$I_C = 50\ \mu\text{A}$
Collector-to-emitter breakdown voltage	BV_{CEO}	60			V	$I_C = 1\ \text{mA}$
Emitter-to-base breakdown voltage	BV_{EBO}	6			V	$I_E = 50\ \mu\text{A}$
Collector cutoff current	I_{CBO}			100	μA	$V_{CB} = 80\ \text{V}$
Emitter cutoff current	I_{EBO}			100	μA	$V_{EB} = 6\ \text{V}$
DC current gain	h_{FE}	400	1000	2000		$V_{CE} = 4\ \text{V}$, $I_C = 0.5\ \text{A}$, single pulse
Collector-to-emitter saturation voltage	$V_{CE(sat)}$		0.3	0.8	V	$I_C/I_B = 2\ \text{A}/0.05\ \text{A}$, single pulse
Collector-to-base saturation voltage	$V_{BE(sat)}$			1.5	V	$I_C/I_B = 2\ \text{A}/0.05\ \text{A}$, single pulse
Transition frequency	f_T		40		MHz	$V_{CE} = 5\ \text{V}$, $I_E = -0.2\ \text{A}$, $f = 10\ \text{MHz}$, single pulse
Output capacitance	C_{ob}		55		pF	$V_{CB} = 10\ \text{V}$, $I_E = 0\ \text{A}$, $f = 1\ \text{MHz}$

h_{FE} rankings

Item	H	J	K
h_{FE}	400 ~ 800	600 ~ 1200	1000 ~ 2000

Electrical characteristic curves

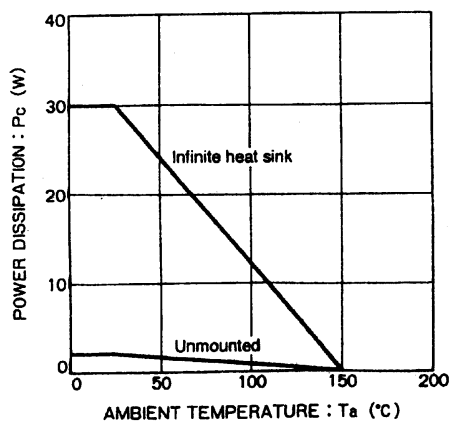


Figure 1

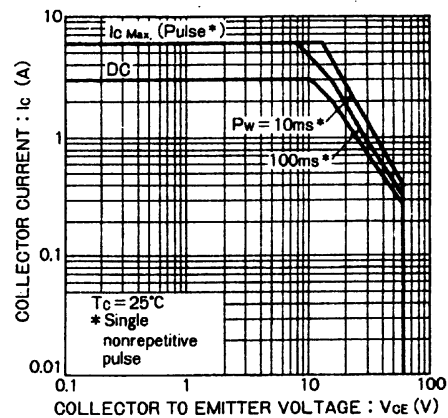


Figure 2

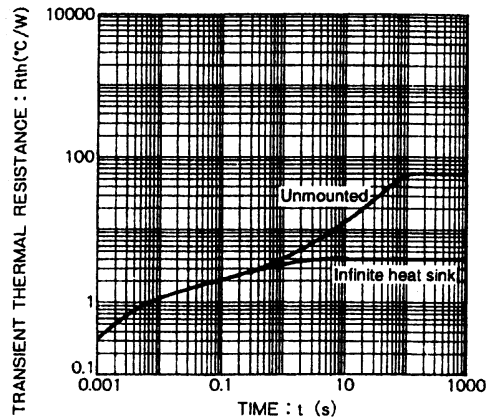


Figure 3

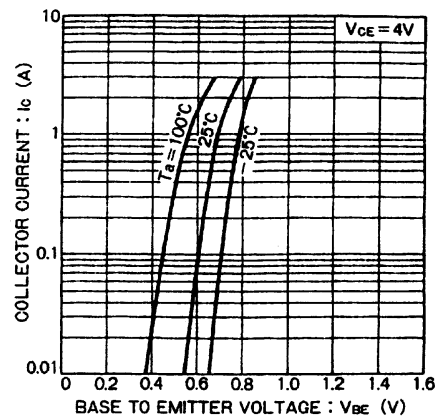


Figure 4

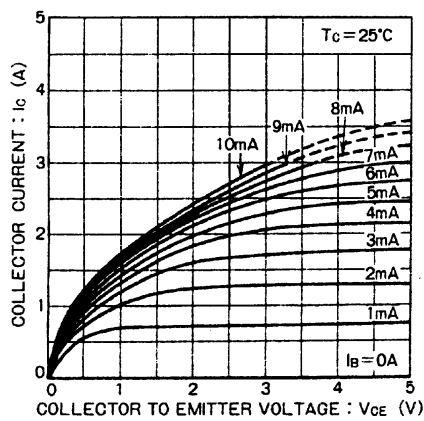


Figure 5

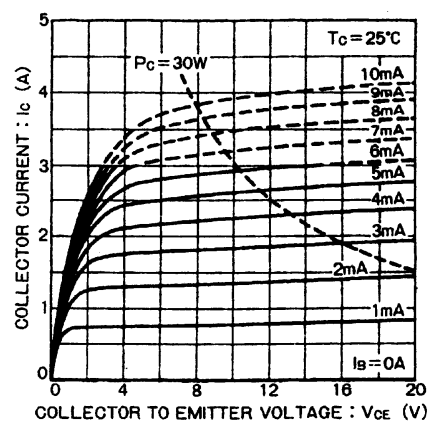


Figure 6

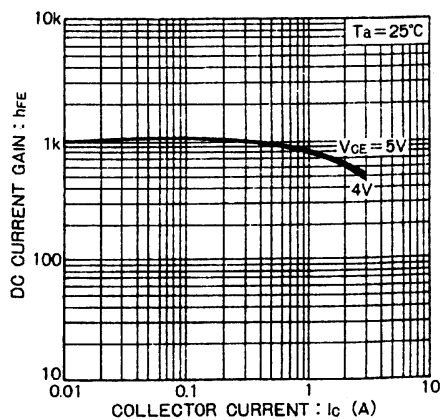


Figure 7

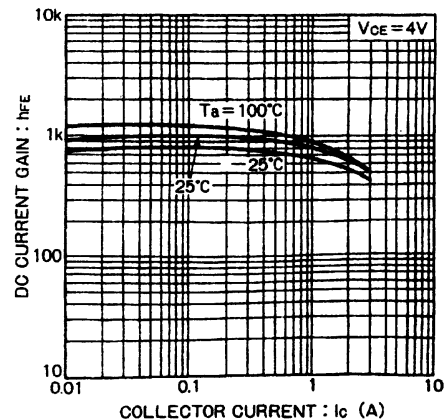


Figure 8

2SD2396 Transistor, NPN, 2SD series

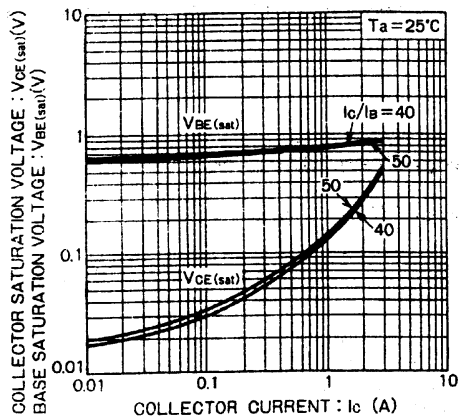


Figure 9

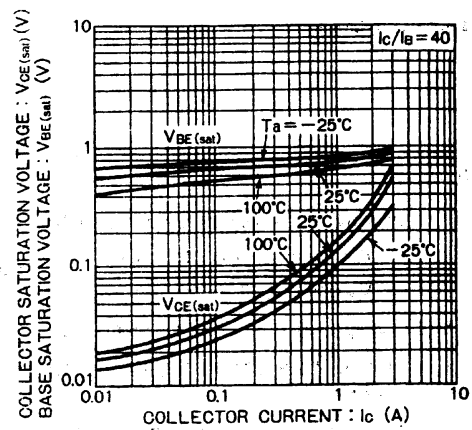


Figure 10

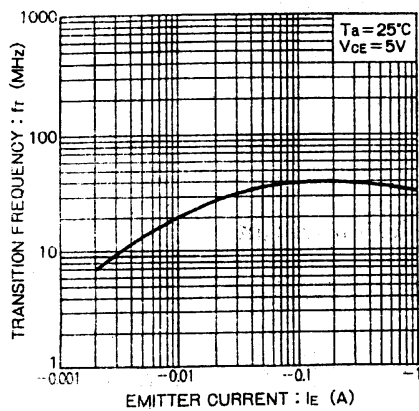


Figure 11

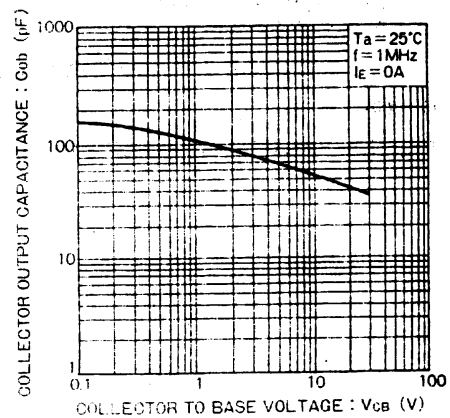


Figure 12

Ordering information

Package	Bulk
Code	
Basic order quantity	500
2SD2396	★
★ = Standard, ☆ = Semi-standard, * = Special order	

Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the product described in this document are for reference only. Upon actual use, therefore, please request that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or otherwise dispose of the same, no express or implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document use silicon as a basic material.
Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

About Export Control Order in Japan

Products described herein are the objects of controlled goods in Annex 1 (Item 16) of Export Trade Control Order in Japan.

In case of export from Japan, please confirm if it applies to "objective" criteria or an "informed" (by MITI clause) on the basis of "catch all controls for Non-Proliferation of Weapons of Mass Destruction.